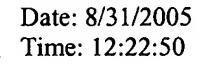
Day: Wednesday



PALMINTRANET

Inventor Name Search Result

Your Search was:

Last Name = SAXLER First Name = ADAM

Application#	Patent#	Status	Date Filed	Title	Inventor Name
11083460	Not Issued	30		LED with substrate modifications for enhanced light extraction and method of making same	SAXLER, ADAM W.
10199454	6841001	150	07/19/2002	STRAIN COMPENSATED SEMICONDUCTOR STRUCTURES AND METHODS OF FABRICATING STRAIN COMPENSATED SEMICONDUCTOR STRUCTURES	SAXLER, ADAM WILLIAM
10199786	Not Issued	71		Strain balanced nitride heterojunction transistors	SAXLER, ADAM WILLIAM
10378331	Not Issued	92	03/03/2003	INTEGRATED NITRIDE- BASED ACOUSTIC WAVE DEVICES AND METHODS OF FABRICATING INTEGRATED NITRIDE-BASED ACOUSTIC WAVE DEVICES	SAXLER, ADAM WILLIAM
10617843	Not Issued	92	07/11/2003	NITRIDE-BASED TRANSISTORS AND METHODS OF FABRICATION THEREOF USING NON- ETCHED CONTACT RECESSES	SAXLER, ADAM WILLIAM
10619228	6875995	150	07/14/2003	HETEROGENEOUS BANDGAP STRUCTURES FOR SEMICONDUCTOR DEVICES AND MANUFACTURING METHODS THEREFOR	SAXLER, ADAM WILLIAM
10640934	Not Issued	83		Nitrogen passivation of interface states in SiO2/SiC structures	SAXLER, ADAM WILLIAM
10707898	Not Issued	71		Silicon Carbide on Diamond Substrates and Related Devices and Methods	SAXLER, ADAM WILLIAM

10752970	Not Issued	71		Co-doping for fermi level control in semi-insulating Group III nitrides	SAXLER, ADAM WILLIAM
10772882	Not Issued	30		Nitride heterojunction transistors having charge-transfer induced energy barriers and methods of fabricating the same	SAXLER, ADAM WILLIAM
10839593	Not Issued	30		Strain compensated semiconductor structures	SAXLER, ADAM WILLIAM
10849589	Not Issued	30		Semiconductor devices having a hybrid channel layer, current aperture transistors and methods of fabricating same	SAXLER, ADAM WILLIAM
<u>10849617</u>	Not Issued	30		Methods of fabricating nitride- based transistors having regrown ohmic contact regions and nitride- based transistors having regrown ohmic contact regions	SAXLER, ADAM WILLIAM
10899215	Not Issued	30		Nitride-based transistors having laterally grown active region and methods of fabricating same	SAXLER, ADAM WILLIAM
10996249	Not Issued	30		Cap layers and/or passivation layers for nitride-based transistors, transistor structures and methods of fabricating same	SAXLER, ADAM WILLIAM
11005107	Not Issued	30		High power density and/or linearity transistors	SAXLER, ADAM WILLIAM
11005423	Not Issued	30		Field effect transistors (FETs) having multi-watt output power at millimeter-wave frequencies	SAXLER, ADAM WILLIAM
11073484	Not Issued	30	03/03/2005	High electron mobility transistor	SAXLER, ADAM WILLIAM
11080905	Not Issued	30	03/15/2005	Group III nitride field effect transistors (FETS) capable of withstanding high temperature reverse bias test conditions	SAXLER, ADAM WILLIAM
11103117	Not Issued	30		Thick semi-insulating or insulating epitaxial gallium nitride layers and devices incorporating same	
11103127	Not Issued	30		Composite substrates of conductive and insulating or semi-insulating group III-nitrides for group III-nitride devices	SAXLER, ADAM WILLIAM
11118575	Not Issued	30		Aluminum free group III-nitride based high electron mobility transistors and methods of	SAXLER, ADAM WILLIAM

				fabricating same	
11118675	Not Issued	30		Binary group III-nitride based high electron mobility transistors and methods of fabricating same	SAXLER, ADAM WILLIAM
11149664	Not Issued	20		Highly uniform group III nitride epitaxial layers on 100 millimeter diameter silicon carbide substrates	SAXLER, ADAM WILLIAM
11169471	Not Issued	19		Low dislocation density group III nitride layers on silicon carbide substrates and methods of making the same	SAXLER, ADAM WILLIAM
60331792	Not Issued	159	11/20/2001	Semi-insulating interlayer structure	SAXLER, ADAM WILLIAM
60337687	Not Issued	159		Strain balanced nitride heterojunction transistor	SAXLER, ADAM WILLIAM
60396236	Not Issued	159		Contacts in a regrowth recess for nitride based transistors and methods of fabricating contacts for nitride based transistors using a regrowth recess	SAXLER, ADAM WILLIAM
60403947	Not Issued	159	08/16/2002	Heterogeneous bandgap structures for semiconductor devices and manufacturing methods therefor	SAXLER, ADAM WILLIAM
60406753	Not Issued	159		Nitrogen passivation of interface states in SiO2/SiC structures	SAXLER, ADAM WILLIAM

Inventor Search Completed: No Records to Display.

Search Another: Inventor	Last Name	First Name	
Search Another: Inventor	SAXLER	ADAM	Search

To go back use Back button on your browser toolbar.

Back to PALM | ASSIGNMENT | OASIS | Home page